

SOT-23 Formed SMD Package

CSA1162

LOW FREQUENCY GENERAL PURPOSE AMPLIFIER TRANSISTOR

P-N-P transistor

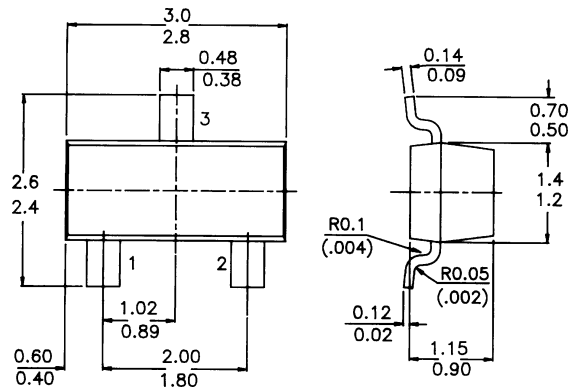
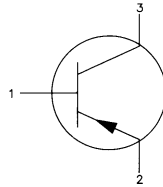
Marking

CSA1162Y-3E
CSA1162GR(G)-3F

PACKAGE OUTLINE DETAILS
ALL DIMENSIONS IN mm

Pin configuration

- 1 = BASE
- 2 = EMITTER
- 3 = COLLECTOR



ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	50 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	50 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	150 mA
Total power dissipation at $T_{amb} = 25^\circ C$	P_{tot}	max.	150 mW
Junction temperature	T_j	max.	150 °C
D.C. current gain	h_{FE}	min.	70
$-I_C = 2 \text{ mA}; -V_{CE} = 6V$		max.	400

RATINGS (at $T_A = 25^\circ C$ unless otherwise specified)

Limiting values			
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	50 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	50 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	150 mA
Base current	$-I_B$	max.	30 mA

Total power dissipation at $T_{amb} = 25^{\circ}C$	P_{tot}	max.	150 mW
Storage temperature	T_{stg}	-50 to +150	$^{\circ}C$
Junction temperature	T_j	max.	150 $^{\circ}C$

CHARACTERISTICS (at $T_A = 25^{\circ}C$ unless otherwise specified)

Collector-emitter breakdown voltage

$-I_C = 1 \text{ mA}; I_B = 0$	$-V_{(BR)CEO}$	min.	50 V
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Collector cut-off current

$-V_{CB} = 50 \text{ V}; I_E = 0$	$-I_{CBO}$	max.	100 nA
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Emitter cut-off current

$V_{EB} = 5 \text{ V}; I_C = 0$	I_{EBO}	max.	100 nA
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Saturation voltage

$-I_C = 100 \text{ mA}; -I_B = 10 \text{ mA}$	$-V_{CEsat}$	max.	0.3 V
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D.C. current gain

$I_C = 2 \text{ mA}; -V_{CE} = 6 \text{ V}$	h_{FE}	min.	70
		max.	400
	Y	min.	120
		max.	240
	$GR(G)$	min.	200
		max.	400

Transition frequency

$V_{CE} = 10 \text{ V}; I_C = 1 \text{ mA}$	f_T	min.	80 MHz
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Collector output capacitance

$V_{CB} = 10 \text{ V}; I_E = 0; f = 1 \text{ MHz}$	C_{ob}	max.	7 pF
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Noise figure

$V_{CE} = 6 \text{ V}; I_C = 0.1 \text{ mA}$ $f = 1 \text{ kHz}; R_g = 10 \text{ k}\Omega$	N_F	max.	10 dB
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Disclaimer

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Continental Device India Limited

C-120 Naraina Industrial Area, New Delhi 110 028, India.
Telephone + 91-11-579 6150 Fax + 91-11-579 9569, 579 5290
e-mail sales@cdil.com www.cdil.com